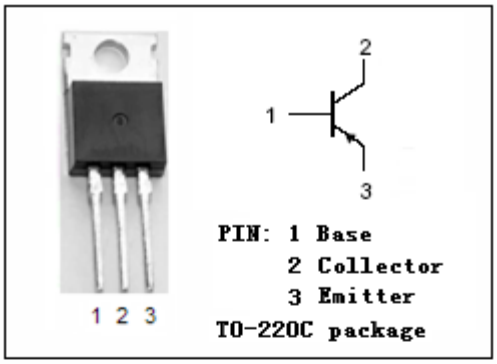
isc Silicon PNP Power Transistor 2SB719



DESCRIPTION

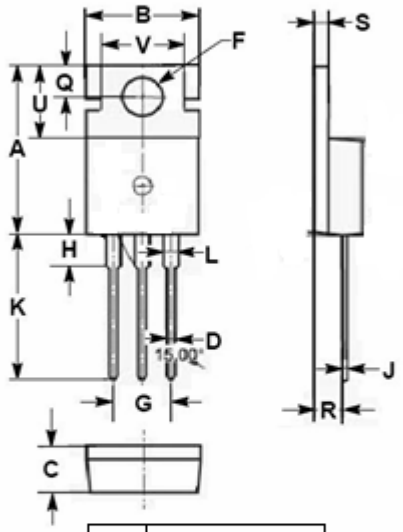
- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -160V(Min)
- Wide Area of Safe Operation
- Complement to Type 2SD759

APPLICATIONS

- Designed for power amplifier and TV vertical deflection output applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-3	A
P_C	Total Power Dissipation@ T_C=25℃	25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.10	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -5mA; I_B= 0	-160			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -0.1mA; I_E= 0	-160			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -0.1mA; I_C= 0	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -500mA; I_B= -50mA			-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -500mA; I_B= -50mA			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -150V; I_E= 0			-10	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= -3.0V; I_C=0			-10	μ A
h_{FE}	DC Current Gain	I_C= -150mA; V_{CE}= -5V	35		200	
f_T	Current-Gain—Bandwidth Product	I_C= -100mA; V_{CE}= -10V		100		MHz

◆ **h_{FE} Classifications**

A	B	C
35-70	60-120	100-200